

2812



PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:
MANFRED HORSTMANN
ROLF STEPHAN
KARSTEN WIECZOREK
STEPHEN KRUEGEL

Examiner: Unknown

Group Art Unit: 2812

Serial No.: 09/847,622


Att'y Docket: 2000.064200/DE0053

Filed: May 2, 2001

For: FIELD EFFECT TRANSISTOR WITH
REDUCED GATE DELAY AND
METHOD OF FABRICATING THE
SAME

PRELIMINARY AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

CERTIFICATE OF MAILING 37 C.F.R. 1.8	
I hereby certify that this correspondence is being deposited with the U.S. Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231, on the date below:	
October 1, 2001 _____ Date	 _____ Signature

Sir:

Please amend the above-referenced patent application as follows:

IN THE CLAIMS:

Please amend claim 1 as follows:

- (Amended) A transistor, comprising:
 a substrate;
 an active region defined in said substrate;
 a gate insulation layer formed above said active region; and
 a gate electrode formed above said gate insulation layer, said gate electrode having a middle portion located over the active region, said middle portion having a gate

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